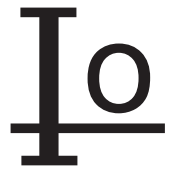


MMBT8050

TRANSISTOR(NPN)

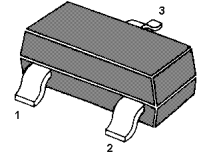


FEATURES

As complementary type the PNP transistor MMBT8550 is recommended.

MARKING: Y1

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1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

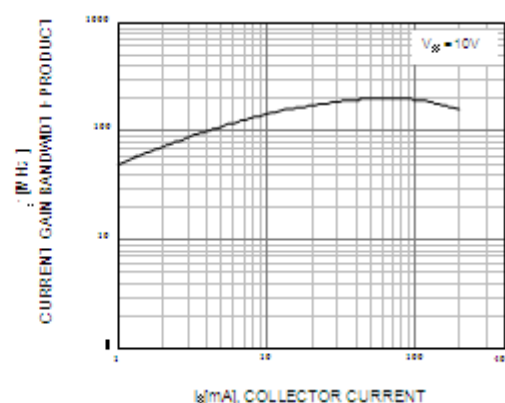
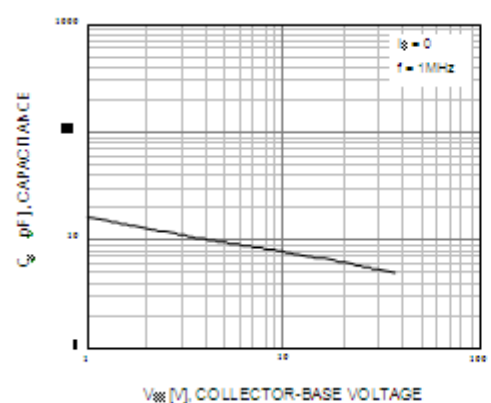
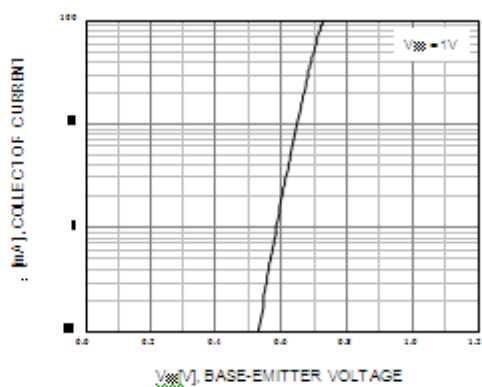
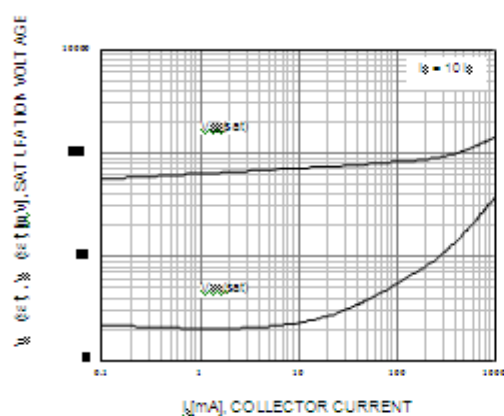
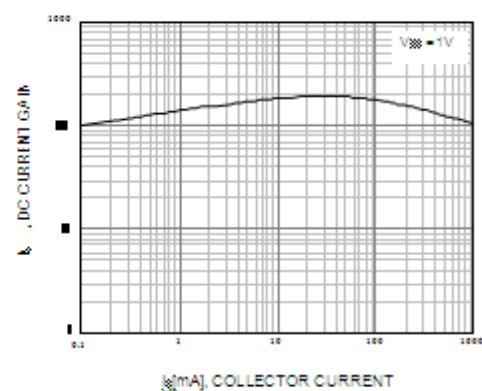
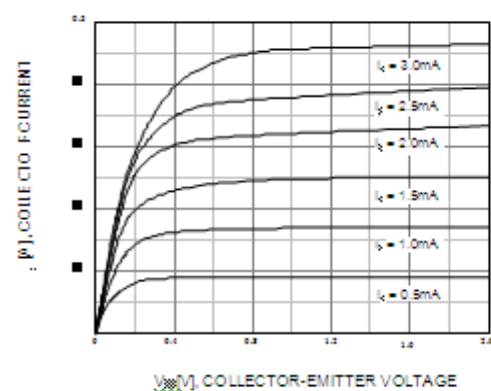
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$, $I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{mA}$, $I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}$, $I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\text{V}$, $I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB} = 20\text{V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1\text{V}$, $I_C = 100\text{mA}$	200		350	
	$h_{FE(2)}$	$V_{CE} = 1\text{V}$, $I_C = 800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 800\text{mA}$, $I_B = 80\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 800\text{mA}$, $I_B = 80\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 10\text{V}$, $I_C = 50\text{mA}$ $f = 30\text{MHz}$	100			MHz

Typical Characteristics

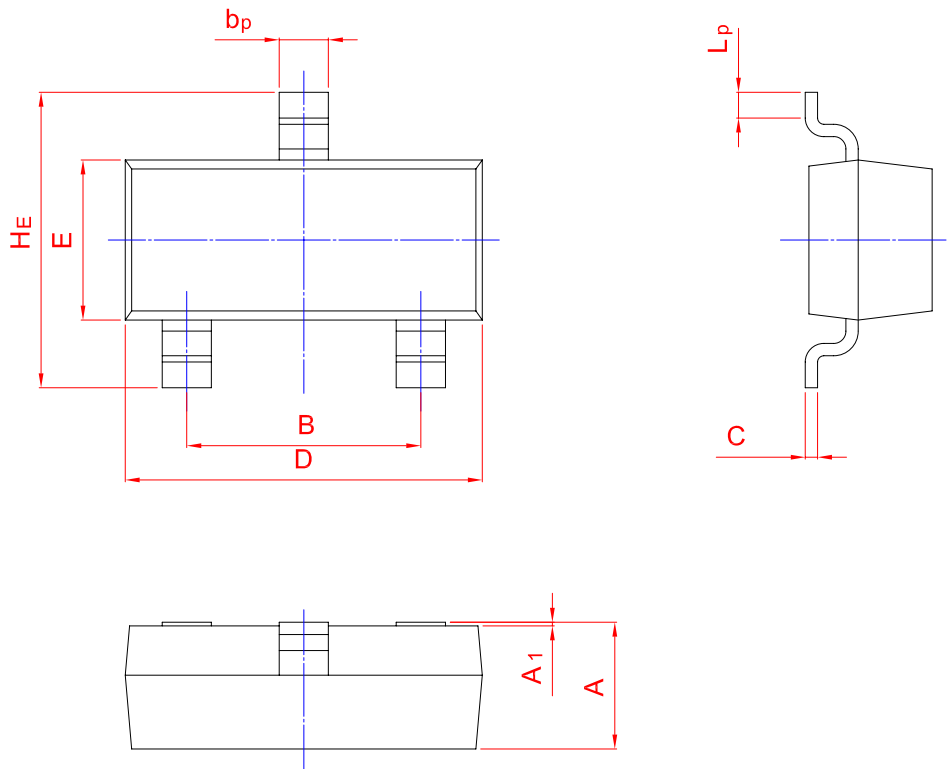
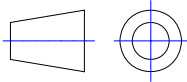
MMBT8050



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20